

Guanhua Yang

List of Publications by Year in descending order

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Version: 2024-02-01

10
papers

304
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1163117

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10
times ranked

600
citing authors

#	ARTICLE	IF	CITATIONS
1	Photoelectric Plasticity in Oxide Thin Film Transistors with Tunable Synaptic Functions. <i>Advanced Electronic Materials</i> , 2018, 4, 1800556.	5.1	94
2	Charge Transfer within the F ₄ TCNQ/MoS ₂ van der Waals Interface: Toward Electrical Properties Tuning and Gas Sensing Application. <i>Advanced Functional Materials</i> , 2018, 28, 1806244.	14.9	62
3	Spike Encoding with Optic Sensory Neurons Enable a Pulse Coupled Neural Network for Ultraviolet Image Segmentation. <i>Nano Letters</i> , 2020, 20, 8015-8023.	9.1	59
4	Room Temperature-Processed a-IGZO Schottky Diode for Rectifying Circuit and Bipolar 1D1R Crossbar Applications. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 4087-4091.	3.0	22
5	A Dual-Functional IGZO-Based Device With Schottky Diode Rectifying and Resistance Switching Behaviors. <i>IEEE Electron Device Letters</i> , 2019, 40, 24-27.	3.9	20
6	Study of Positive-Gate-Bias-Induced Hump Phenomenon in Amorphous Indium-Gallium-Zinc Oxide Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 1606-1612.	3.0	16
7	Bulk-Like Electrical Properties Induced by Contact-Limited Charge Transport in Organic Diodes: Revised Space Charge Limited Current. <i>Advanced Electronic Materials</i> , 2018, 4, 1700493.	5.1	15
8	Thickness of accumulation layer in amorphous indium-gallium-zinc-oxide thin-film transistors by Kelvin Probe Force Microscopy. <i>Applied Physics Letters</i> , 2019, 114, .	3.3	11
9	Optimization of Electrical Properties of MoS ₂ Field-Effect Transistors by Dipole Layer Coulombic Interaction With Trap States. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019, 13, 1900007.	2.4	5
10	A Direct n ⁺ -Formation Process by Magnetron Sputtering an Inter-Layer Dielectric for Self-Aligned Coplanar Indium Gallium Zinc Oxide Thin-Film Transistors. <i>Micromachines</i> , 2022, 13, 652.	2.9	0